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# HL6319/20G

AlGaInP Laser Diodes

## HITACHI

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### Description

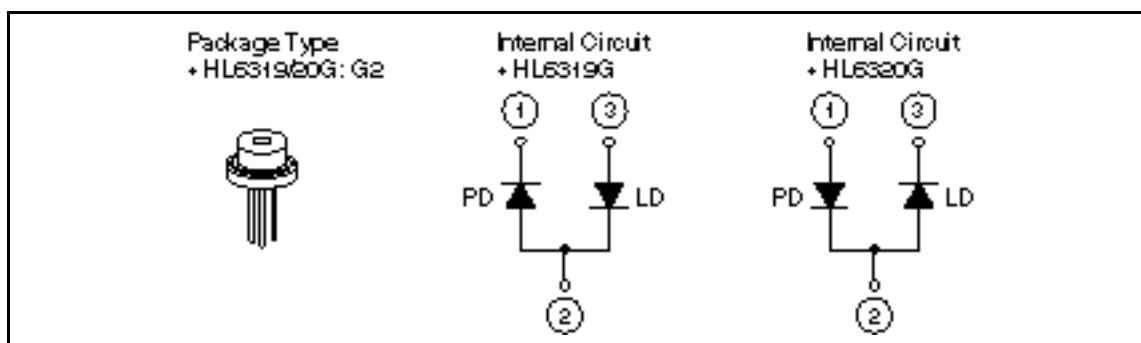
The HL6319/20G are 0.63  $\mu\text{m}$  band AlGaInP laser diodes with a multi-quantum well (MQW) structure. They are suitable as light sources for laser levelers and optical equipment for measurement.

### Application

- Laser levelers
- Measurement

### Features

- Visible light output: 635nm Typ (nearly equal to He-Ne gas laser)
- Optical output power: 10 mW CW
- Low operating current: 95 mA Max
- Low operating voltage: 2.7 V Max



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## HL6319/20G

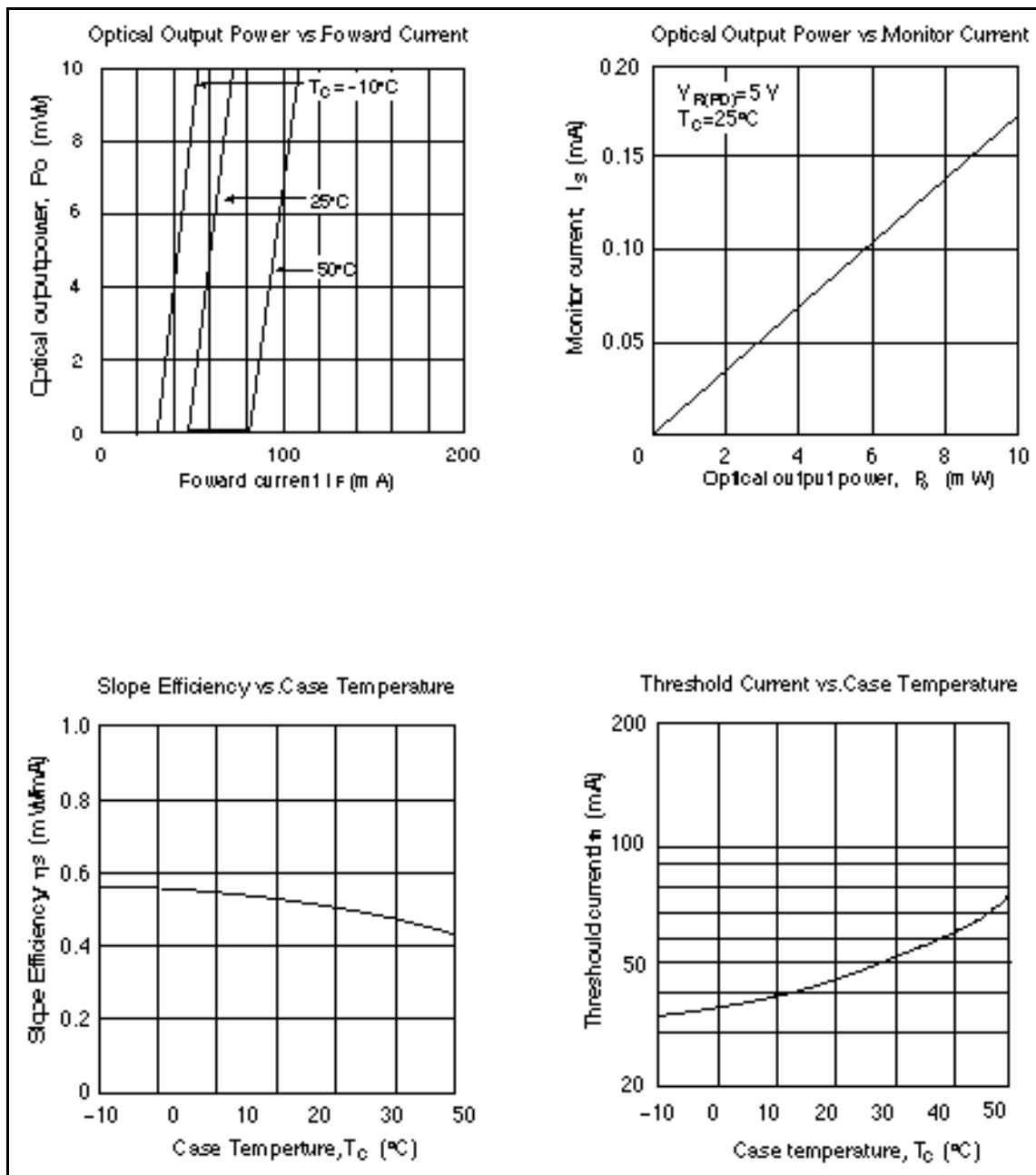
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### Absolute Maximum Ratings ( $T_C = 25^\circ\text{C}$ )

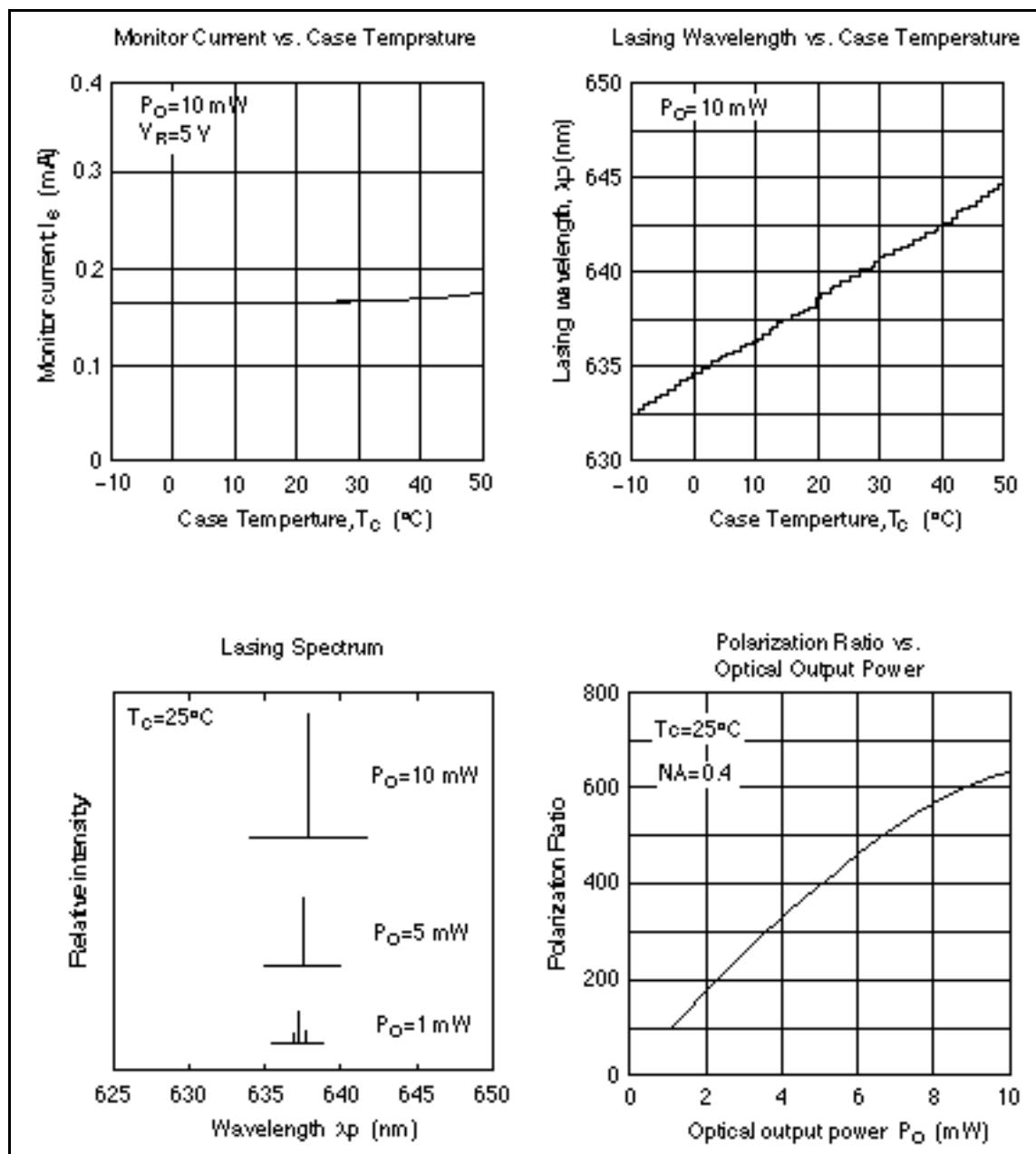
Item	Symbol	Value	Unit
Optical output power	$P_o$	10	mW
LD reverse voltage	$V_{R(LD)}$	2	V
PD reverse voltage	$V_{R(PD)}$	30	V
Operating temperature	$T_{opr}$	-10 to +50	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-40 to +85	$^\circ\text{C}$

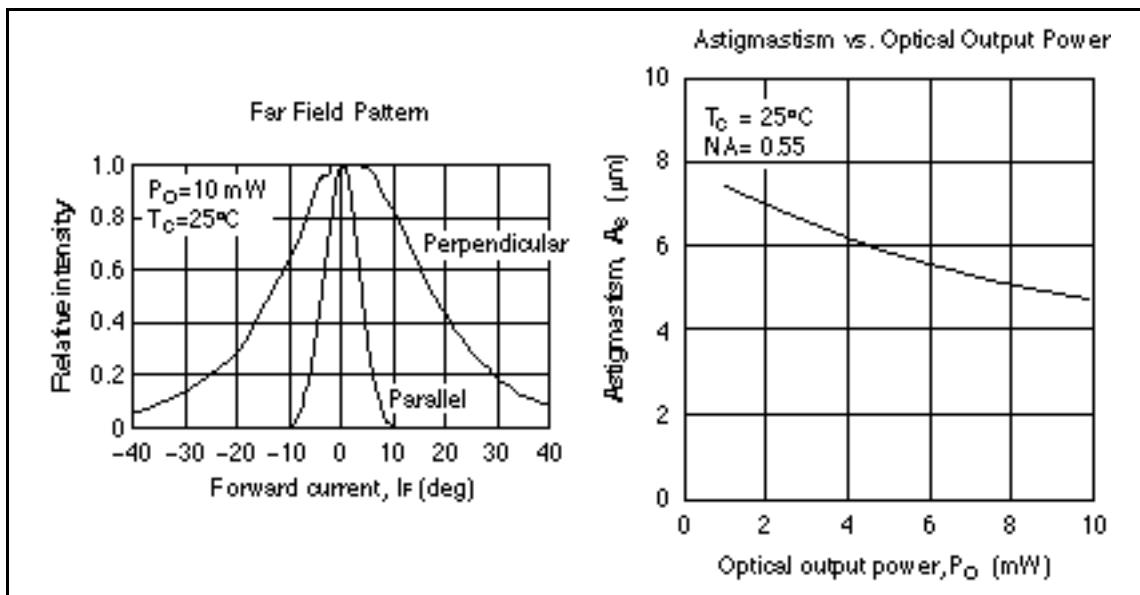
### Optical and Electrical Characteristics ( $T_C = 25^\circ\text{C}$ )

Item	Symbol	Min	Typ	Max	Unit	Test Conditions
Optical output power	$P_o$	10	—	—	mW	Kink free
Threshold current	$I_{th}$	20	50	75	mA	
Operating current	$I_{op}$	—	70	95	mA	$P_o = 10 \text{ mW}$
Operating voltage	$V_{op}$	—	—	2.7	V	$P_o = 10 \text{ mW}$
Slope efficiency	$s$	0.3	0.5	0.7	mW/mA	$6(\text{mW})/(I(8\text{mW})-I(2\text{mW}))$
Lasing wavelength	$\lambda$	625	635	640	nm	$P_o = 10 \text{ mW}$
Beam divergence (parallel)	//	5	8	11	deg.	$P_o = 10 \text{ mW}$
Beam divergence (perpendicular)		25	31	37	deg.	$P_o = 10 \text{ mW}$
Monitor current	$I_s$	0.05	0.17	0.30	mA	$P_o = 10 \text{ mW}, V_{R(PD)} = 5 \text{ V}$

**Typical Characteristics Curves**

## HL6319/20G





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### **Polarization direction**

The polarization direction is TM mode. The polarization of 0.63  $\mu\text{m}$  LD's is different from that of 0.83/0.78/0.67  $\mu\text{m}$  LD's. The polarization direction of 0.63  $\mu\text{m}$  LD's is illustrated in the figure below.

